

Cathkin High School Physics Department CfE Higher

## Unit 3 Electricity



## Learning Outcomes

Name		
INUME	 	••••

Class.....

I am confident that I understand this and I can apply this to problems
 I have some understanding but I need to revise this some more
 I don't know this or I need help because I don't understand it

Covered How well you do th			
(*)	×	?	✓
	×	?	✓
	×	?	✓
	×	?	✓
	×	?	✓
	×	?	✓
	×	?	✓
		you (*) * * * * * * * *	you do ti (*) * ? * ? * ? * ? * ? * ? * ? * ?

Section 1 Electrons and Energy	lectrons and Energy Covered		Section 1 Electrons and Energy Covered How you			
Current, voltage, power and resistance	(*)	x	?	✓		
<ol> <li>State that voltage is defined as the energy transformed per unit of charge.</li> </ol>		×	?	<b>√</b>		
8. State the relationship V = $E_w/Q$ .		*	?	✓		
9. Carry out calculations involving the relationship between energy, voltage and charge.		*	?	✓		
10. State that the energy transformed from an external source to the circuit is known as the electromotive force (e.m.f.).		×	?	✓		
11. Give examples of sources of e.m.f.		×	?	✓		
12. State that the energy transformed into another form of energy by a circuit component is known as the potential difference (p.d.).		×	?	✓		
13. Carry out calculations involving the relationships between power, current, voltage and resistance in series and parallel circuits.		*	?	✓		
14. State that a potential divider circuit consists of a number of resistors, or other components, connected across a supply.		×	?	~		
15. Carry out calculations involving potential differences and resistances in potential dividers using the potential divider equation and Ohm's law.		*	?	✓		

Section 1 Electrons and Energy	Covered	How we you do t		
Electrical sources and internal resistance	(~)	x	?	✓
16. State that a power supply is equivalent to a source of e.m.f. with a resistor in series, the internal resistance.		×	?	✓
17. Describe the principles of a method for measuring the e.m.f. and internal resistance of a source		×	?	<b>√</b>
18. Explain why the e.m.f. of a source is equal to the open circuit p.d. across the terminals of a source.		×	?	<b>√</b>
19. State that the closed circuit p.d. across the terminals of a source is equal to the t.p.d.		×	?	✓
20. State that the e.m.f. of a cell is equal to the sum of the t.p.d. and the lost volts.		×	?	✓
21. Carry out calculations involving the relationship between the e.m.f., t.p.d. and lost volts.		×	?	✓
22. Describe two methods of measuring e.m.f. and internal resistance by graphical methods.		×	?	✓
23. State the R = r for maximum transfer of energy between a source and a load.		×	?	<b>√</b>

Section 1 Electrons and Energy	Covered		How well ca you do this	
Capacitors	(✓)	×	?	✓
24. State that the capacitance of a capacitor is a measure of its ability to store charge.		×	?	✓
25. State that a simple capacitor consists of two parallel conducting plates separated by an air gap.		×	?	✓
26. Describe the circuit symbol for a capacitor.		×	?	✓
27. State that the charge Q stored on a capacitor is directly proportional to the p.d. V across it.		×	?	✓
28. Describe the principles of a method to show that the p.d. across a capacitor is directly proportional to the charge on the plates.		×	?	✓
29. State that capacitance is defined as the gradient of the charge against p.d. graph or the ratio of charge to p.d.		×	?	✓
30. State that the unit of capacitance is the farad and that one farad is one coulomb per volt.		×	?	✓
31. Carry out calculations involving the relationship between charge, capacitance and p.d.		×	?	✓
32. Explain why work must be done to charge a capacitor.		×	?	✓

Section 1 Electrons and Energy	Covered		v well ı do tl	
Capacitors (continued)	(~)	×	?	✓
33. State that the work done to charge a capacitor is given by the area under the graph of charge against p.d.		×	?	✓
<ul> <li>34. State that the energy stored in a capacitor is given by ½ (charge × p.d.) and equivalent expressions.</li> </ul>		×	?	✓
35. Carry out calculations using the relationship between energy, charge and p.d. or alternative expressions.		×	?	✓
36. Draw qualitative graphs of current against time and of voltage against time for the charge and discharge of a capacitor in a d.c. circuit containing a resistor and capacitor in series.		×	?	✓
37. Carry out calculations involving voltage and current in CR circuits.		×	?	✓

Section 2 Electrons at work	Covered		How well o you do thi	
Conductors, semiconductors and insulators	(*)	x	?	√
1. State that solids can be classified into three types according to their electrical properties as conductors, semiconductors and insulators.		×	?	✓
2. Give examples of conductors, semiconductors and insulators.		×	?	✓
3. State that the different electrical properties of conductors, semiconductors and insulators can be explained by Band Theory.		×	?	✓
4. State that in isolated atoms, the permitted energy levels consist of a series of sharply defined states.		×	?	✓
5. State that in solids, the permitted energy levels associated with each state of the isolated atom forms a continuous band.		×	?	✓
<ol> <li>State that the two highest bands are known as the valence band and the conduction band, respectively.</li> </ol>		×	?	✓
7. State that the valence band contains electrons that can be considered to be bound to the atom.		×	?	✓
8. State that the valence band is full in insulators and semiconductors.		×	?	✓
9. State that the conduction band contains electrons that are free to move.		×	?	✓
10. State that the conduction band is empty in insulators and semiconductors, but partially filled in conductors.		×	?	✓

Section 2 Electrons at work	Covered		v well ı do tl	
Conductors, semiconductors and insulators (continued)	(*)	×	?	✓
11. State that only partially filled bands may permit conduction.		×	?	✓
12. State that there is an energy gap between the valence and conduction bands in insulators and semiconductors.		×	?	✓
13. State that an electron can absorb energy to move between the valence band and the conduction band.		×	?	✓
14. State that in insulators, the energy gap is normally too large for electrons to jump to the conduction band.		×	?	✓
15. State that in semiconductors, the energy gap is much smaller and electrons can jump to the conduction band as a result of thermal excitation.		×	?	•

Section 2 Electrons at work	Covered	-	v well ı do ti	
Intrinsic and extrinsic semiconductors	(*)	×	?	√
16. State that in semiconductors, conduction occurs by means of negative charge carriers, (electrons) or positive charge carriers (holes).		×	?	<b>√</b>
17. State that in pure semiconductors there are very few electrons available to conduct which makes the resistance very large.		×	?	✓
<ol> <li>State that in pure semiconductors more free electrons become available at higher temperatures, therefore the conductivity increases and the resistance decreases.</li> </ol>		×	?	✓
19. State that these pure semiconductors are known as <b>intrinsic</b> semiconductors.		×	?	✓
20. State that the addition of impurity atoms to a pure semiconductor (a process called doping) increases its conductivity by adding either extra electrons or holes to the lattice.		×	?	✓
21. State that doped semiconductors now have a majority charge carrier present and are known as <b>extrinsic</b> semiconductors.		×	?	✓
22. State that group V doping agents result in n-type extrinsic semiconductors, which contain extra electrons.		×	?	✓
23. State that group III doping agents result in p-type extrinsic semiconductors, which contain extra holes.		×	?	✓

24. Explain how doping can form an n-type semiconductor in which the majority of the charge carriers are negative, or a p-type semiconductor in which the majority of the charge carriers are positive.	×	?	~

Section 2 Electrons at work	Covered		v well ı do tl	
p – n junctions	(*)	×	?	✓
25. State that the interface between p-type and n-type material is called the p-n junction and it functions as a diode.		×	?	✓
<ol> <li>State that the majority charge carriers diffuse towards the junction and electrons and holes combine to form ions.</li> </ol>		×	?	✓
<ul> <li>27. State that this results in a depletion zone across the p-n junction where the density of charge carriers is low, with positive ions on the n-type side and negative ions on the p-type side.</li> </ul>		×	?	✓
28. State that when the p-type material is connected to the positive terminal of a supply and the n-type to the negative terminal, then the junction is <b>forward biased</b> .		×	?	✓
29. State that if the potential difference across the junction is sufficient to force electrons to cross the depletion zone, then the junction will conduct.		×	?	✓
30. State that when the terminals are reversed, the junction is <b>reverse biased</b> and cannot conduct.		×	?	<b>√</b>

Section 2 Electrons at work	Covered		v well ı do tl	
p – n junctions (continued)	(√)	×	?	√
31. Describe the movement of the charge carriers in a forward/ reverse-biased p-n junction diode.		×	?	<ul> <li>✓</li> </ul>
32. State that in a light emitting diode a large forward bias is applied to the p-n junction enabling positive and negative charge carriers to recombine, thereby producing photons of light.		×	?	✓
33. State that the frequency of the emitted photons increases as the size of the energy gap between the conduction and valence bands increases.		×	?	✓
34. State the relationship $E = h f$ .		×	?	✓
35. Carry out calculations involving the relationships between E, h, f and λ.		×	?	<b>√</b>
36. State that in photovoltaic cells, absorbed photons can create electron-hole pairs to produce a potential difference.		×	?	<b>√</b>